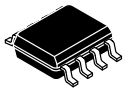
CM1213

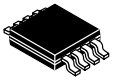
6 and 8-Channel Low Capacitance ESD Protection Arrays

ON Semiconductor®

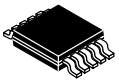
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SOIC−8
SM SUFFIX
CASE 751AC



MSOP−8
MR SUFFIX
CASE 846AD



MSOP−10
MR SUFFIX
CASE 846AE

Product Description

The CM1213 family of diode arrays has been designed to provide ESD protection for electronic components or sub−systems requiring minimal capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes in series which steer the positive or negative ESD current pulse to either the positive (V_P) or negative (V_N) supply rail. A Zener diode is embedded between V_P and V_N, offering two advantages. First, it protects the V_{CC} rail against ESD strikes, and second, it eliminates the need for a bypass capacitor that would otherwise be needed for absorbing positive ESD strikes to ground. The CM1213 will protect against ESD pulses up to ±8 kV per the IEC 61000−4−2 standard.

These devices are particularly well−suited for protecting systems using high−speed ports such as USB2.0, IEEE1394 (Firewire®, iLink™), Serial ATA, DVI, HDMI and corresponding ports in removable storage, digital camcorders, DVD−RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

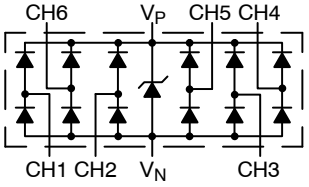
Features

- 6 or 8 Channels of ESD Protection
  Note: For 1, 2, and 4 Channel Devices, See the CM1213A Datasheet
- Provides ESD Protection to IEC61000−4−2 Level 4
  - ±8 kV Contact Discharge
- Low Channel Input Capacitance of 1.0 pF Typical
- Minimal Capacitance Change with Temperature and Voltage
- Channel Input Capacitance Matching of 0.02 pF Typical is Ideal for Differential Signals
- Mutual Capacitance between Signal Pin and Adjacent Signal Pin −0.11 pF Typical
- Zener Diode Protects Supply Rail and Eliminates the Need for External By−pass Capacitors
- Each I/O Pin Can Withstand Over 1000 ESD Strikes*
- Available in SOIC and MSOP
- These Devices are Pb−Free and are RoHS Compliant

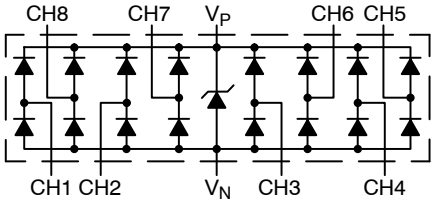
Applications

- USB2.0 Ports at 480 Mbps in Desktop PCs, Notebooks and Peripherals
- IEEE1394 Firewire® Ports at 400 Mbps / 800 Mbps
- DVI Ports, HDMI Ports in Notebooks, Set Top Boxes, Digital TVs, LCD Displays
- Serial ATA Ports in Desktop PCs and Hard Disk Drives
- PCI Express Ports
- General Purpose High−speed Data Line ESD Protection
- Handheld PCs/PDAs

BLOCK DIAGRAMS



CM1213−06SM
CM1213−06MR



CM1213−08MR

ORDERING INFORMATION

Device	Package	Shipping†
CM1213−06SM	SOIC−8 (Pb−Free)	2500/Tape & Reel
CM1213−06MR	MSOP−8 (Pb−Free)	4000/Tape & Reel
CM1213−08MR	MSOP−10 (Pb−Free)	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*Standard test condition is IEC61000−4−2 level 4 test circuit with each pin subjected to ±8 kV contact discharge for 1000 pulses. Discharges are timed at 1 second intervals and all 1000 strikes are completed in one continuous test run. The part is then subjected to standard production test to verify that all of the tested parameters are within spec after the 1000 strikes.

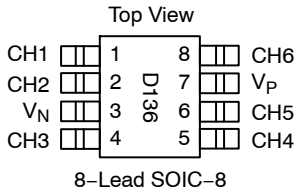
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Table 1. PIN DESCRIPTIONS

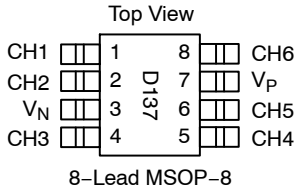
6−Channel, 8−Lead MSOP−8/SOIC−8 Packages			
Pin	**Name**	**Type**	**Description**
1	CH1	I/O	ESD Channel
2	CH2	I/O	ESD Channel
3	V_N	GND	Negative voltage supply rail
4	CH3	I/O	ESD Channel
5	CH4	I/O	ESD Channel
6	CH5	I/O	ESD Channel
7	V_P	PWR	Positive voltage supply rail
8	CH6	I/O	ESD Channel

8−Channel, 10−Lead MSOP−10 Package			
Pin	**Name**	**Type**	**Description**
1	CH1	I/O	ESD Channel
2	CH2	I/O	ESD Channel
3	CH3	I/O	ESD Channel
4	CH4	I/O	ESD Channel
5	V_N	GND	Negative voltage supply rail
6	CH5	I/O	ESD Channel
7	CH6	I/O	ESD Channel
8	V_P	PWR	Positive voltage supply rail
9	CH7	I/O	ESD Channel
10	CH8	I/O	ESD Channel

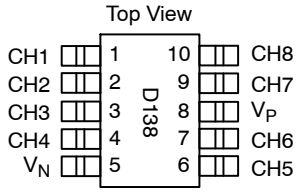
PACKAGE / PINOUT DIAGRAMS



8−Lead SOIC−8



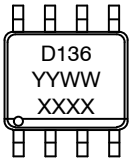
8−Lead MSOP−8



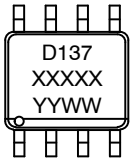
10−Lead MSOP−10

GENERIC MARKING DIAGRAMS

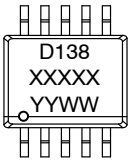
CM1213−06SM



CM1213−06MR



CM1213−08MR



XXXXX = Lot Number
YY = Year
WW = Work Week

SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Operating Supply Voltage (V_P – V_N)	6.0	V
Operating Temperature Range	−40 to +85	°C
Storage Temperature Range	−65 to +150	°C
DC Voltage at any channel input	(V_N – 0.5) to (V_P + 0.5)	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. STANDARD OPERATING CONDITIONS

Parameter	Rating	Units
Operating Temperature Range	−40 to +85	°C
Package Power Rating MSOP−8 Package (CM1213−06MR) MSOP−10 Package (CM1213−08MR) SOIC−8 Package (CM1213−06SM)	 400 400 600	mW

Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_P	Operating Supply Voltage (V_P–V_N)			3.3	5.5	V
I_P	Operating Supply Current	(V_P–V_N) = 3.3 V			8.0	μA
V_F	Diode Forward Voltage Top Diode Bottom Diode	I_F = 8 mA; T_A = 25°C	 0.60 0.60	 0.80 0.80	 0.95 0.95	V
I_{LEAK}	Channel Leakage Current	T_A = 25°C; V_P = 5 V, V_N = 0 V		±0.1	±1.0	μA
C_{IN}	Channel Input Capacitance	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V		1.0	1.5	pF
ΔC_{IN}	Channel Input Capacitance Matching	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V		0.02		pF
C_{MUTUAL}	Mutual Capacitance between signal pin and adjacent signal pin	At 1 MHz, V_P = 3.3 V, V_N = 0 V, V_{IN} = 1.65 V		0.11		pF
V_{ESD}	ESD Protection Peak Discharge Voltage at any channel input, in system Contact discharge per IEC 61000−4−2 standard	 T_A = 25°C (Notes 3 and 4)	 ±8			kV
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	T_A = 25°C, I_{PP} = 1 A, t_P = 8/20 μS (Note 4)		 +8.8 −1.4		V
R_{DYN}	Dynamic Resistance Positive Transients Negative Transients	I_{PP} = 1 A, t_P = 8/20 μS Any I/O pin to Ground (Note 4)		 0.7 0.4		Ω

1. All parameters specified at T_A = −40°C to +85°C unless otherwise noted.
2. Human Body Model per MIL−STD−883, Method 3015, $C_{Discharge}$ = 100 pF, $R_{Discharge}$ = 1.5 KΩ, V_P = 3.3 V, V_N grounded.
3. Standard IEC 61000−4−2 with $C_{Discharge}$ = 150 pF, $R_{Discharge}$ = 330 Ω, V_P = 3.3 V, V_N grounded.
4. These measurements performed with no external capacitor on V_P (V_P floating).

PERFORMANCE INFORMATION

Input Channel Capacitance Performance Curves

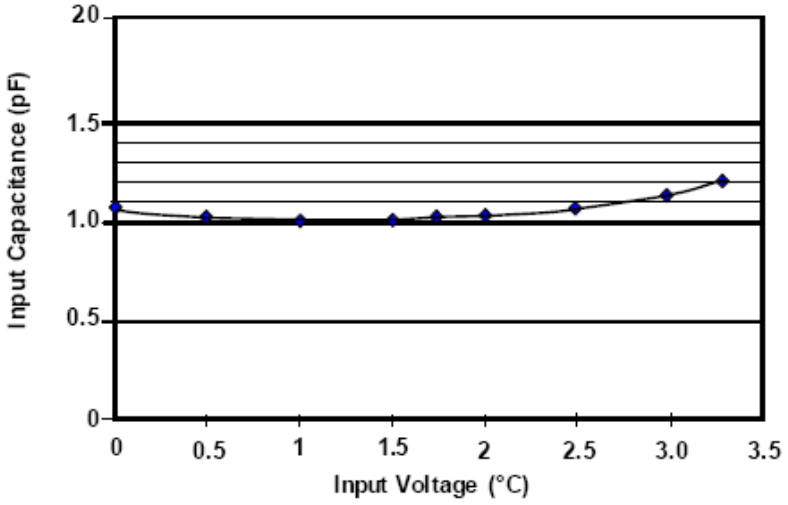


Figure 1. Typical Variation of C_{IN} vs. V_{IN}
(f = 1 MHz, V_P = 3.3 V, V_N = 0 V, 0.1 μF Chip Capacitor between V_P and V_N, 25°C)

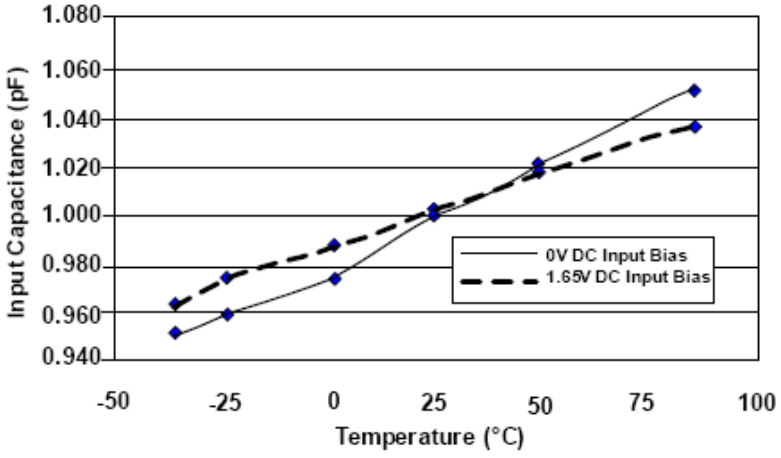


Figure 2. Typical Variation of C_{IN} vs. Temp
(f = 1 MHz, V_{IN} = 30 mV, V_P = 3.3 V, V_N = 0 V, 0.1 μF Chip Capacitor between V_P and V_N)

PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance (Nominal Conditions unless Specified Otherwise, 50 Ohm Environment)

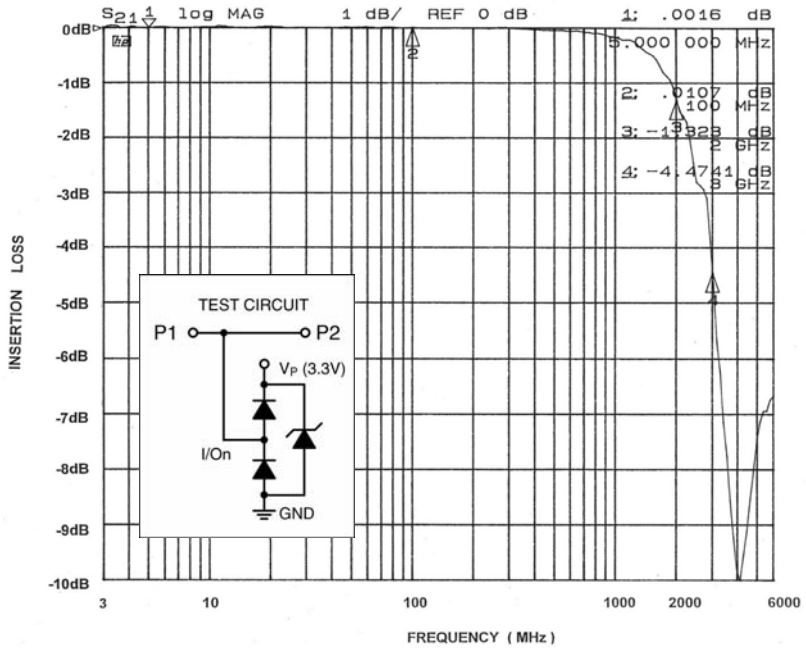


Figure 3. Insertion Loss (S21) vs. Frequency (0 V DC Bias, V_P=3.3 V)

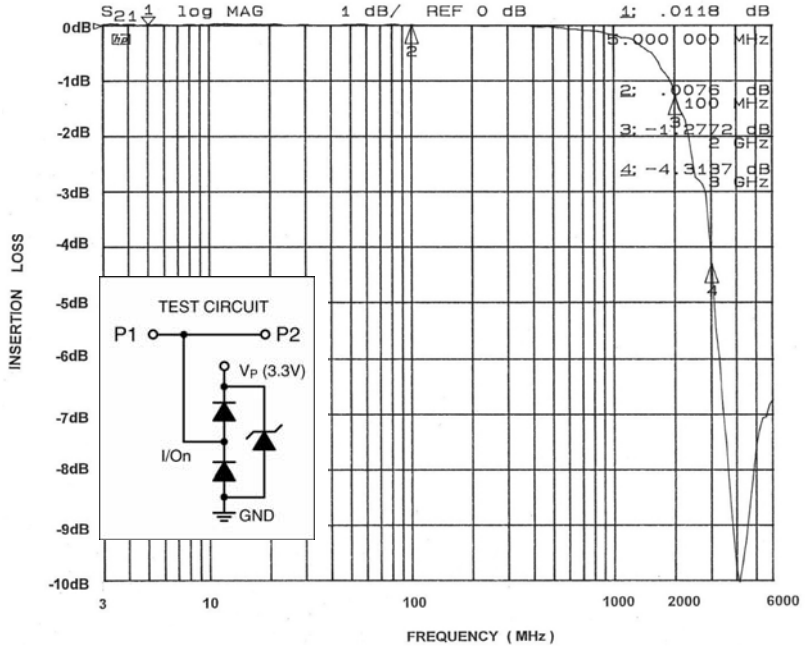


Figure 4. Insertion Loss (S21) vs. Frequency (2.5 V DC Bias, V_P=3.3 V)

APPLICATION INFORMATION

Design Considerations

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Application of Positive ESD Pulse between Input Channel and Ground, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to power supply is represented by L_1 and L_2. The voltage V_{CL} on the line being protected is:

$$\mathbf{V_{CL} = Fwd\ voltage\ drop\ of\ D_1 + V_{SUPPLY} + L_1 \times d(I_{ESD}) / dt + L_2 \times d(I_{ESD}) / dt}$$

where I_{ESD} is the ESD current pulse, and V_{SUPPLY} is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000−4−2 standard results in a current pulse that rises from zero to 30 Amps in 1 ns. Here $d(I_{ESD})/dt$ can be approximated by $\Delta I_{ESD}/\Delta t$, or $30/(1x10^{-9})$. So just 10 nH of series inductance (L_1 and L_2 combined) will lead to a 300 V increment in V_{CL}!

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

The CM1213 has an integrated Zener diode between V_P and V_N. This greatly reduces the effect of supply rail inductance L_2 on V_{CL} by clamping V_P at the breakdown voltage of the Zener diode. However, for the lowest possible V_{CL}, especially when V_P is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a 0.22 μF ceramic chip capacitor be connected between V_P and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the V_P pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

Additional Information

See also ON Semiconductor Application Note, “Design Considerations for ESD Protection”, in the Applications section.

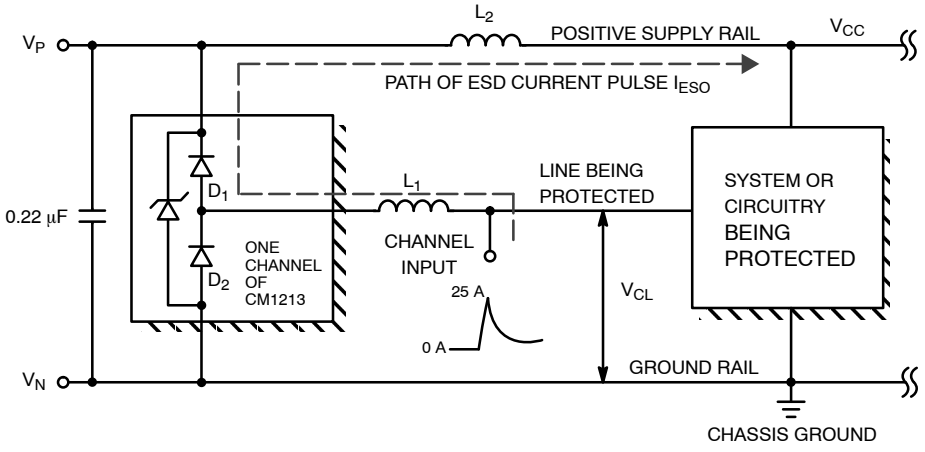
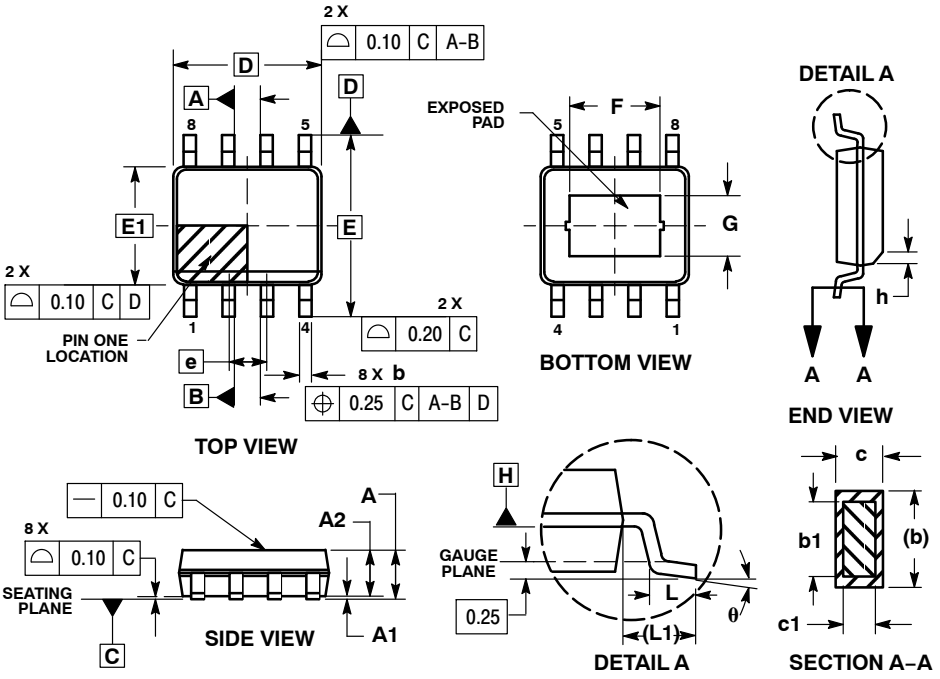


Figure 5. Application of Positive ESD Pulse between Input Channel and Ground

PACKAGE DIMENSIONS

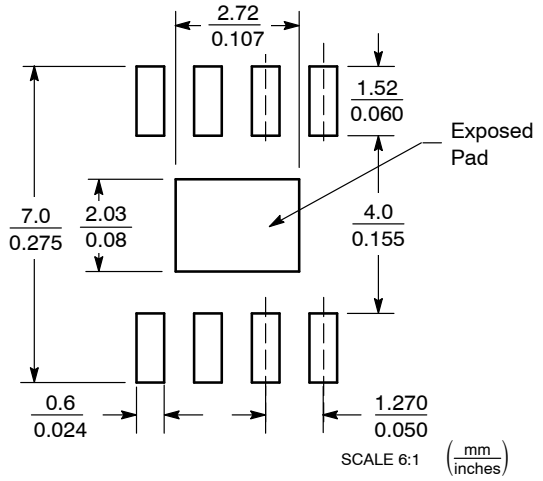
SOIC−8 EP
CASE 751AC
ISSUE B



NOTES:
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. DIMENSIONS IN MILLIMETERS (ANGLES IN DEGREES).
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 MM TOTAL IN EXCESS OF THE “b” DIMENSION AT MAXIMUM MATERIAL CONDITION.
4. DATUMS A AND B TO BE DETERMINED AT DATUM PLANE H.

	MILLIMETERS	
DIM	MIN	MAX
A	1.35	1.75
A1	0.00	0.10
A2	1.35	1.65
b	0.31	0.51
b1	0.28	0.48
c	0.17	0.25
c1	0.17	0.23
D	4.90 BSC	
E	6.00 BSC	
E1	3.90 BSC	
e	1.27 BSC	
L	0.40	1.27
L1	1.04 REF	
F	2.24	3.20
G	1.55	2.51
h	0.25	0.50
θ	0 °	8 °

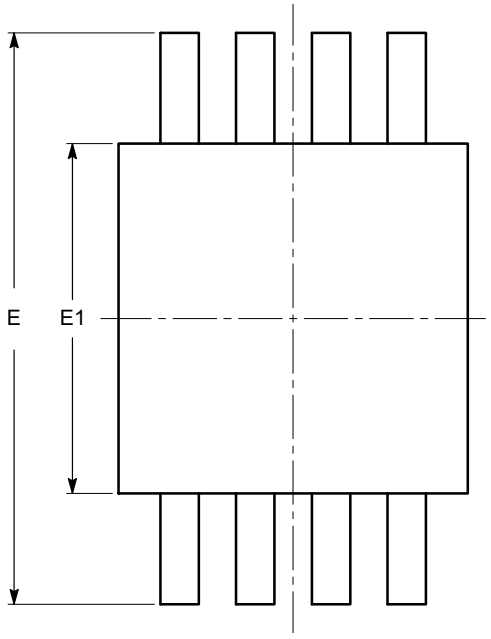
SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

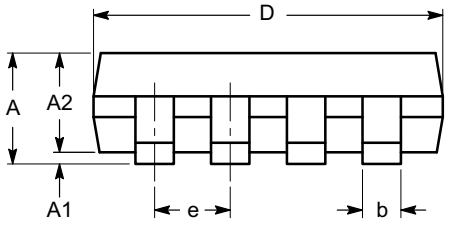
PACKAGE DIMENSIONS

MSOP 8, 3x3
CASE 846AD
ISSUE O

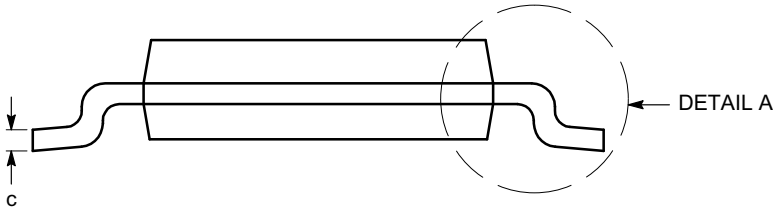


TOP VIEW

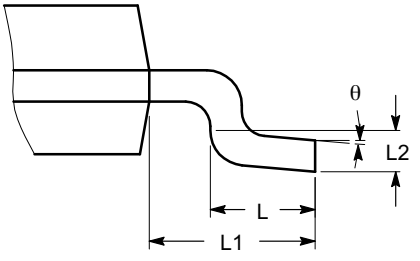
SYMBOL	MIN	NOM	MAX
A			1.10
A1	0.05	0.10	0.15
A2	0.75	0.85	0.95
b	0.22		0.38
c	0.13		0.23
D	2.90	3.00	3.10
E	4.80	4.90	5.00
E1	2.90	3.00	3.10
e	0.65 BSC		
L	0.40	0.60	0.80
L1	0.95 REF		
L2	0.25 BSC		
θ	0°		6°



SIDE VIEW



END VIEW

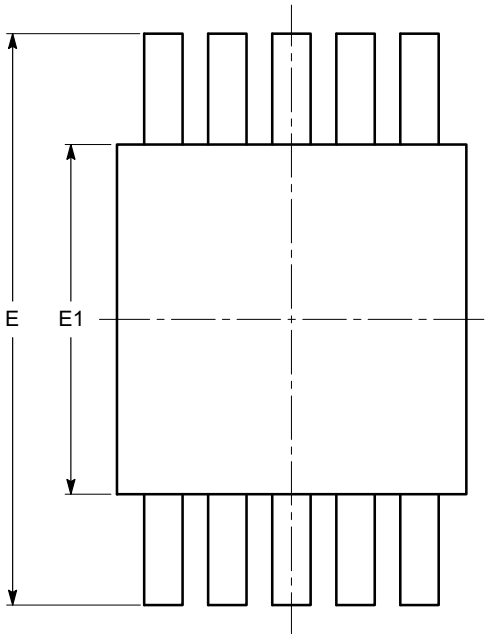


DETAIL A

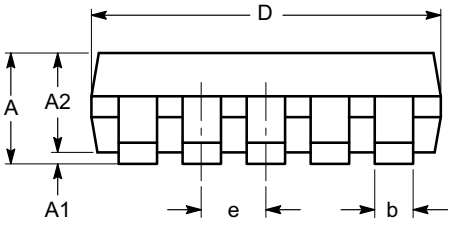
Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-187.

PACKAGE DIMENSIONS

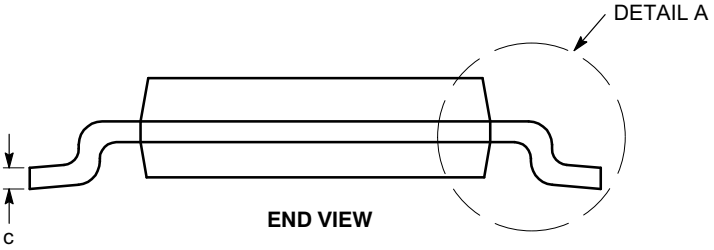
MSOP 10, 3x3
CASE 846AE
ISSUE O



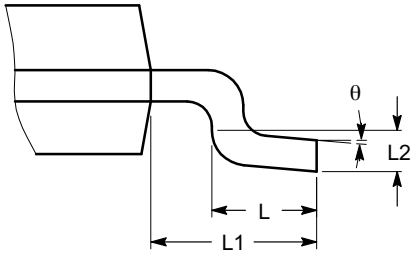
TOP VIEW



SIDE VIEW



END VIEW



DETAIL A

SYMBOL	MIN	NOM	MAX
A			1.10
A1	0.00	0.05	0.15
A2	0.75	0.85	0.95
b	0.17		0.27
c	0.13		0.23
D	2.90	3.00	3.10
E	4.75	4.90	5.05
E1	2.90	3.00	3.10
e		0.50 BSC	
L	0.40	0.60	0.80
L1		0.95 REF	
L2		0.25 BSC	
θ	0°		8°

Notes:
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC MO-187.

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